

SOT-363 Plastic-Encapsulate Transistors

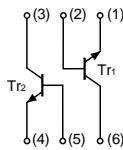
UMX18N General purpose transistors (dual transistors)

FEATURES

- Two 2SC5585 chips in a package
- Mounting possible with SOT-363 automatic mounting machines
- Transistor elements are independent, eliminating interference
- Mounting cost and area be cut in half

Marking: X18

Equivalent circuit



Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	15	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	500	mA
P _C	Collector Power Dissipation	150	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	15			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	12			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =15V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =2V, I _C =10mA	270		680	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =200mA, I _B =10mA			0.25	V
Transition frequency	f _T	V _{CE} =2V, I _E =-10mA, f=100MHz		320		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		7.5		pF